



SEMIPACK® 1

Thyristor / Diode Modules

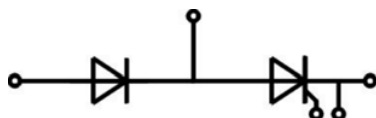
SKKH 92/16 E G6

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- UL recognized, file no. E63532

Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
Chip				
$I_{T(AV)}$	sinus 180°	$T_c = 85\text{ °C}$	98	A
		$T_c = 100\text{ °C}$	74	A
I_{TSM}	10 ms	$T_j = 25\text{ °C}$	2000	A
		$T_j = 130\text{ °C}$	1750	A
i^2t	10 ms	$T_j = 25\text{ °C}$	20000	A ² s
i^2t		$T_j = 130\text{ °C}$	15313	A ² s
V_{RSM}			1700	V
V_{RRM}			1600	V
V_{DRM}			1600	V
$(di/dt)_{cr}$	$T_j = 130\text{ °C}$		140	A/μs
$(dv/dt)_{cr}$	$T_j = 130\text{ °C}$		1000	V/μs
T_j			-40 ... 130	°C
Module				
T_{stg}			-40 ... 125	°C
V_{isol}	a.c.; 50 Hz; r.m.s.	1 min	3000	V
		1 s	3600	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Chip					
V_T	$T_j = 25\text{ °C}, I_T = 300\text{ A}$		1.7	1.85	V
$V_{T(TO)}$	$T_j = 130\text{ °C}$		0.85	0.95	V
r_T	$T_j = 130\text{ °C}$		3.30	4.00	mΩ
$I_{DD}; I_{RD}$	$T_j = 130\text{ °C}, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$			20	mA
t_{gd}	$T_j = 25\text{ °C}, I_G = 1\text{ A}, di_G/dt = 1\text{ A}/\mu\text{s}$		1		μs
t_{gr}	$V_D = 0.67 * V_{DRM}$		2		μs
t_q	$T_j = 130\text{ °C}$		200		μs
I_H	$T_j = 25\text{ °C}$		150	250	mA
I_L	$T_j = 25\text{ °C}, R_G = 33\text{ }\Omega$		300	600	mA
V_{GT}	$T_j = 25\text{ °C}, \text{d.c.}$	2.5			V
I_{GT}	$T_j = 25\text{ °C}, \text{d.c.}$	100			mA
V_{GD}	$T_j = 130\text{ °C}, \text{d.c.}$			0.25	V
I_{GD}	$T_j = 130\text{ °C}, \text{d.c.}$			4	mA
$R_{th(j-c)}$	cont.	per chip		0.230	K/W
		per module		0.115	K/W
$R_{th(j-c)}$	sin. 180°	per chip		0.240	K/W
		per module		0.120	K/W
$R_{th(j-c)}$	rec. 120°	per chip		0.250	K/W
		per module		0.125	K/W
Module					
$R_{th(c-s)}$	chip		0.22		K/W
	module		0.11		K/W
M_s	to heatsink M5	4.25		5.75	Nm
M_t	to terminals M5	2.55		3.45	Nm
a				5 * 9,81	m/s ²
w			75		g

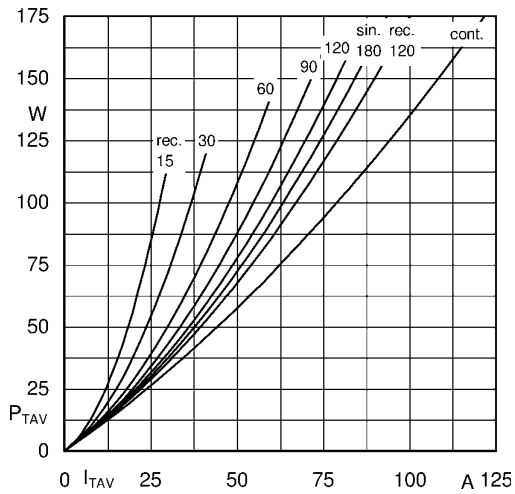


Fig. 1L: Power dissipation per thyristor/diode vs. on-state current

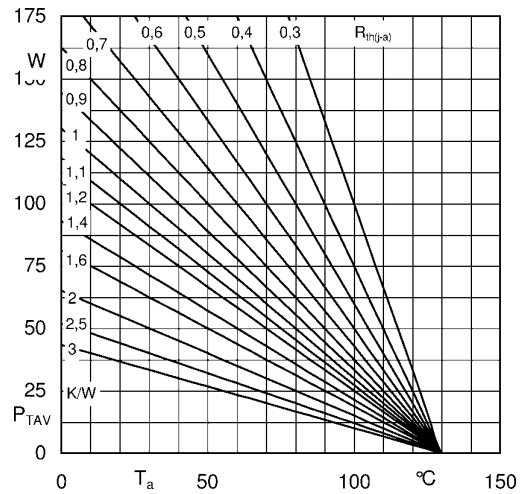


Fig. 1R: Max. power dissipation per chip vs. ambient temperature

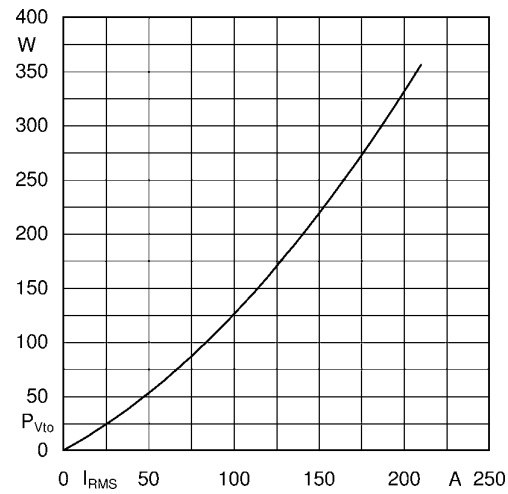


Fig. 2L: Max. power dissipation of one module vs. rms current

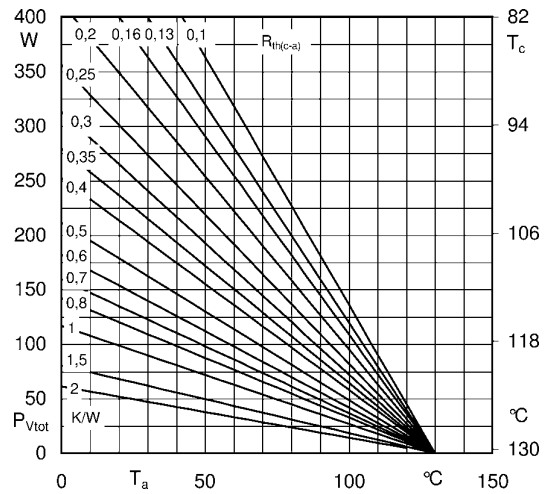


Fig. 2R: Max. power dissipation of one module vs. case temperature

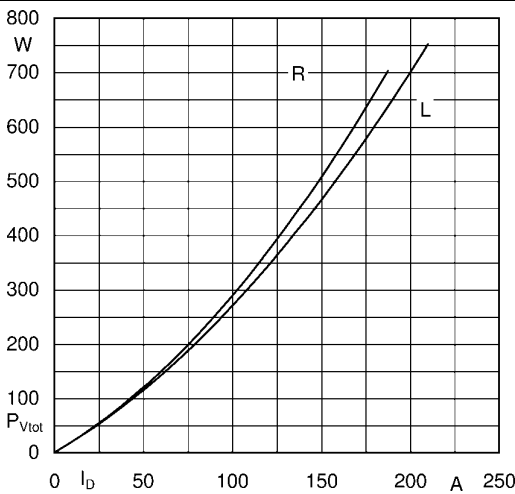


Fig. 3L: Max. power dissipation of two modules vs. direct current

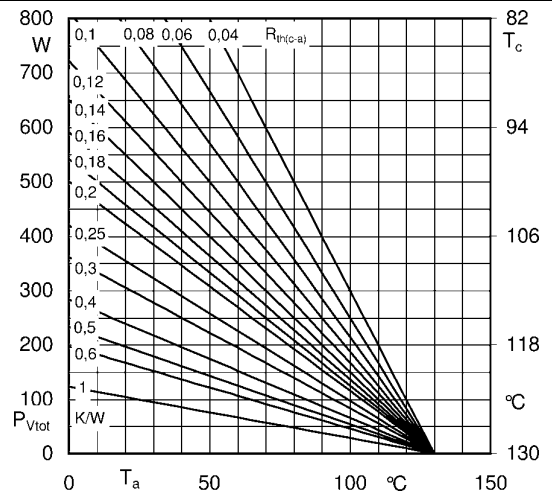


Fig. 3R: Max. power dissipation of two modules vs. case temperature

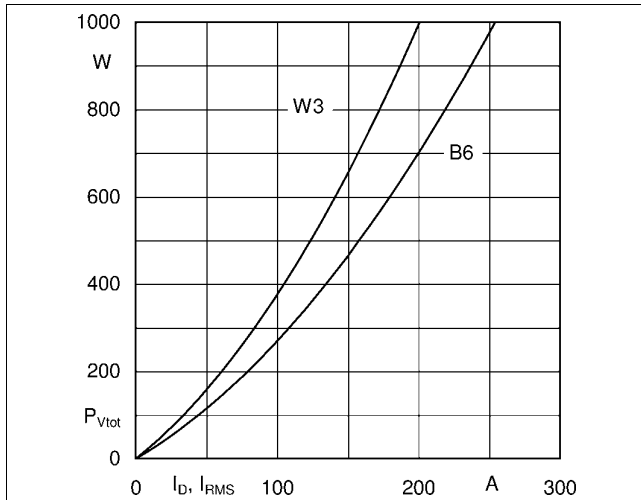


Fig. 4L: Max. power dissipation of three modules vs. direct current

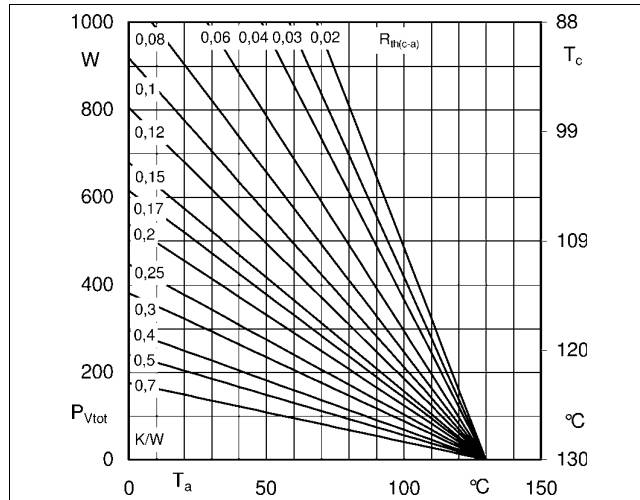


Fig. 4R: Max. power dissipation of three modules vs. case temperature

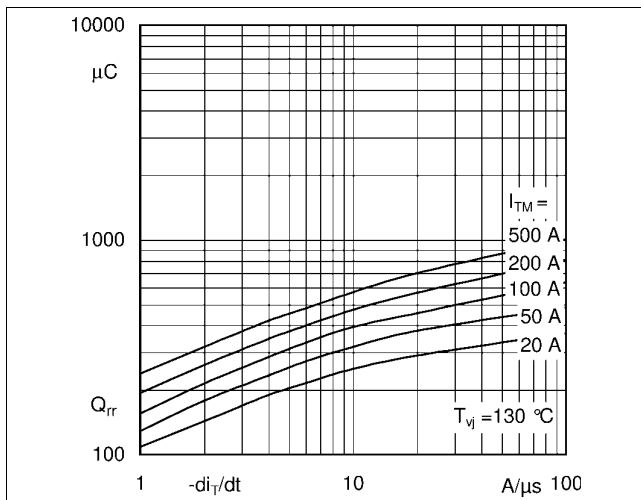


Fig. 5: Recovered charge vs. current decrease

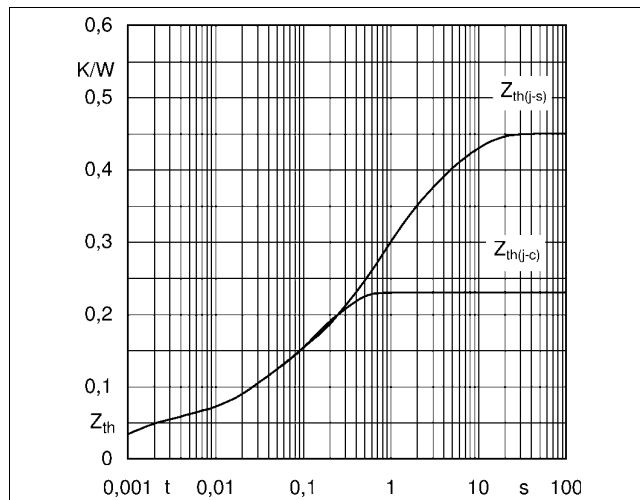


Fig. 6: Transient thermal impedance vs. time

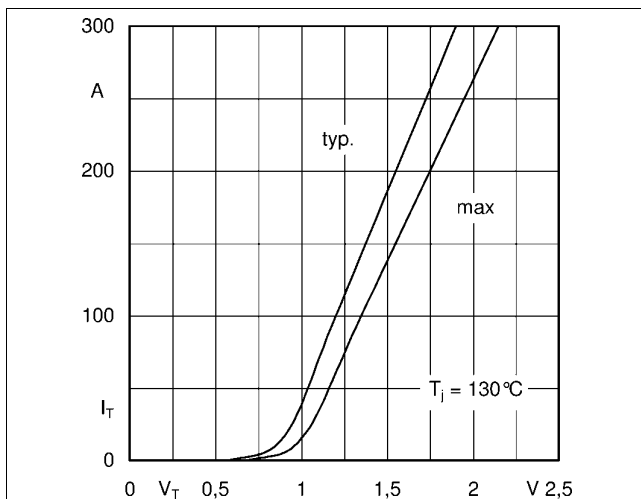


Fig. 7: On-state characteristics

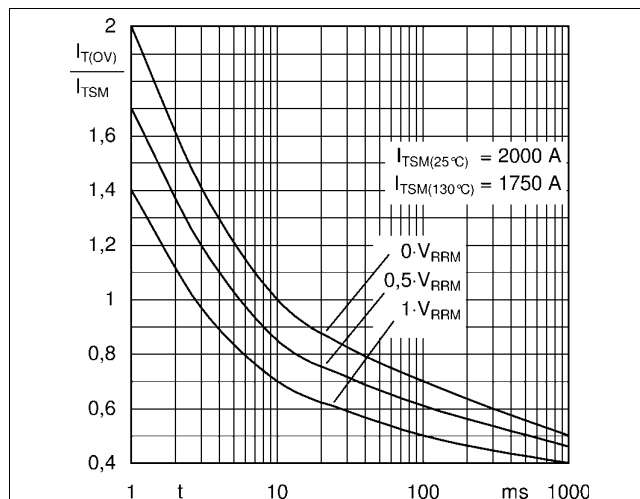


Fig. 8: Surge overload current vs. time

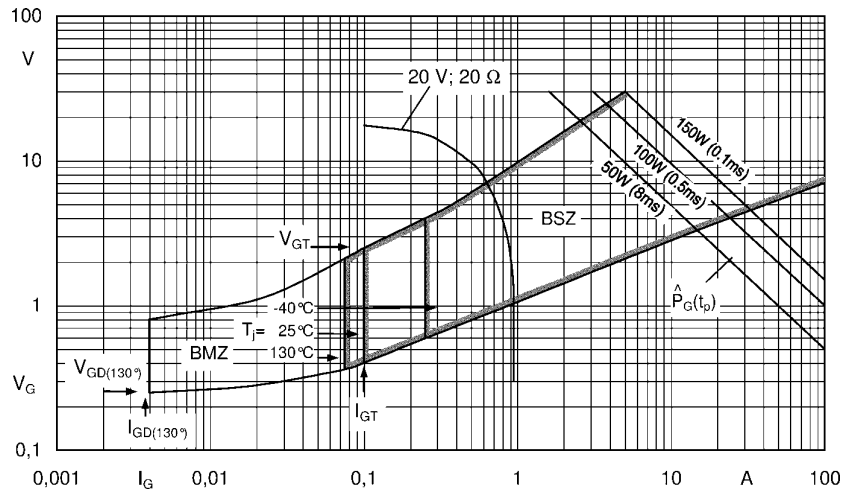
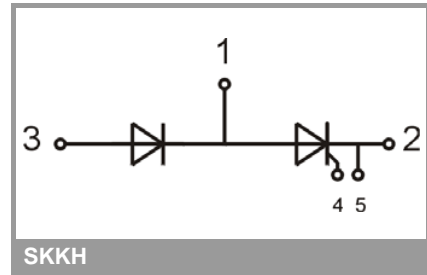
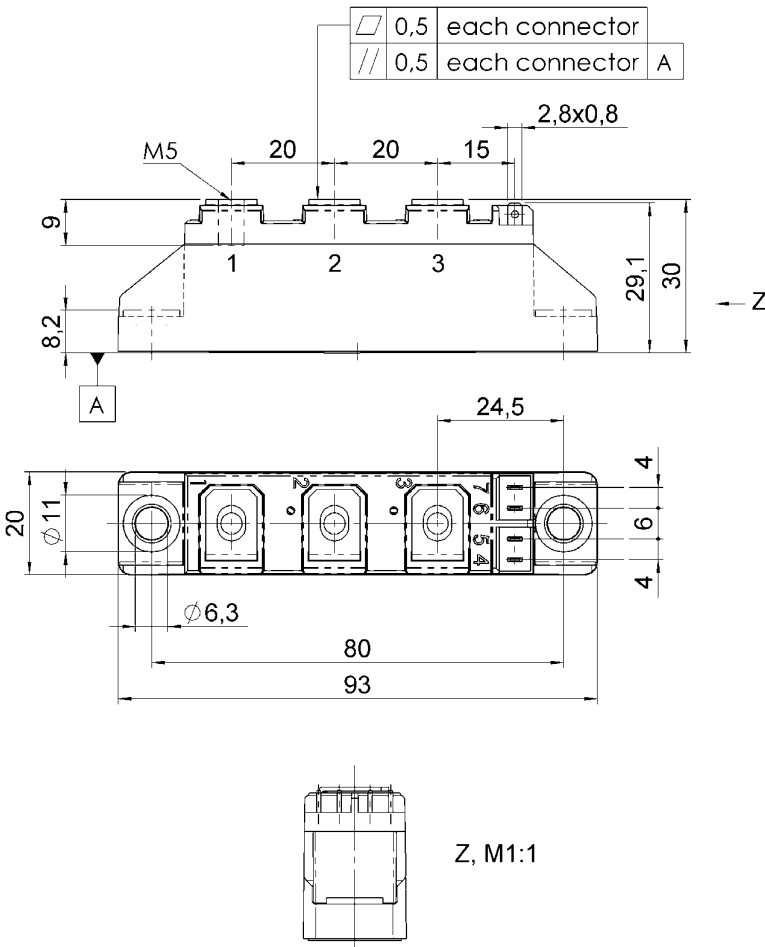


Fig. 9: Gate trigger characteristics



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